

FORM PTO-1449 (REV. 1-84)	U.S. DEPARTMENT OF COMMERCE PATENT & TRADEMARK OFFICE	CASE NO. 13-16	SERIAL NO. <u>10/716 697</u>
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT: Stanley Pau et al.	
		FILING DATE	GROUP <u>2882</u>

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
<u>NO</u>	AA	4 3 4 0 2 8 3	7/82	Cohen	351	161	
<u>NO</u>	AB	5 6 2 8 6 5 9	5/97	Xie et al.	445	3	
<u>NO</u>	AC	6 1 4 8 0 6 1	11/00	Shefer et al.	378	121	
<u>NO</u>	AD	6 2 5 9 7 6 4	7/01	Evans-Lutterodt et al.	378	84	
<u>NO</u>	AE	6 4 4 8 1 0 0	9/02	Schulte et al.	438	20	
<u>NO</u>	AF	6 4 7 7 2 3 3	11/02	Ribbing et al.	378	136	
<u>NO</u>	AG	6 5 9 2 5 2 6	7/03	Lenker	600	463	
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY/AUTHOR	CLASS	SUB- CLASS	TRANSL'N YES NO
	AL						
	AM						
	AN						
	AO						
	AP						

OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>NO</u>	AR	Henke et al., Two-channel, elliptical..., Rev. Sci. Instrum., Vol. 56, No. 8, p. 1537 (Aug. 1985)
<u>NO</u>	AS	Lee et al., High aspect ratio..., J. Vac. Sci. Tech., Vol. B12, No. 6, p. 3425 (Nov/Dec. 1994)
<u>NO</u>	AT	Tang et al., Emission measurements..., J. Vac. Sci. Tech., Vol. B14, No. 6, p. 3455 (Nov/Dec. 1996)
<u>NO</u>	AU	Nagao et al., Metal-oxide-semiconductor..., J. Vac. Sci. Tech., Vol. B21, No. 1, p. 495 (Jan/Feb. 2003)
<u>NO</u>	AV	Busta et al., Characterization of electron..., J. Vac. Sci. Tech., Vol. B21, No. 1, p. 344 (Jan/Feb. 2003)
<u>NO</u>	AW	Evans-Lutterodt et al., Single-element..., Optics Express, Vol. 11, No. 8, p. 919 (Apr. 2003)
	AX	

EXAMINER:

SHEET 1 OF 1

DATE CONSIDERED:

3/18/05